

Product Overview

NTMFD4901NF: Dual N-Channel Power MOSFET with Integrated Schottky 30V,

For complete documentation, see the data sheet.

Dual N-Channel Power MOSFET with Integrated Schottky
30 V, High Side 18 A / Low Side 30 A, Dual N-Channel SO8FL

Features

- Co-Packaged Power Stage Solution to Minimize Board Space
- Low Side MOSFET with Integrated Schottky
- Minimized Parasitic Inductances
- Optimized Devices to Reduce Power Losses
- RoHS Compliant

Applications

- DC-DC Converters
- System Voltage Rails
- Point of Load

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	$V_{DS(S)}^{(BR)}$ Min (V)	V_{GS} Max (V)	$V_{GS(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$R_{DS(on)}$ Max @ $V_{GS} = 2.5$ V (m Ω)	$R_{DS(on)}$ Max @ $V_{GS} = 4.5$ V (m Ω)	$R_{DS(on)}$ Max @ $V_{GS} = 10$ V (m Ω)	Q_g Typ @ $V_{GS} = 4.5$ V (nC)	Q_g Typ @ $V_{GS} = 10$ V (nC)	C_{iss} Typ (pF)	Package Type
NTMFD4901NFT1G	0.9113	Pb-free Halide free	Active	N-Channel	Dual	30	20	2.2	18.2	1.9	-	Q1: 10, Q2: 3.5	Q1: 6.5, Q2: 2.35	63	9.7	Q1: 1150, Q2: 2950	SO-8FL Dual / DFN-8
NTMFD4901NFT3G	0.9113	Pb-free Halide free	Active	N-Channel	Dual	30	20	2.2	18.2	1.9	-	Q1: 10, Q2: 3.5	Q1: 6.5, Q2: 2.35	63	9.7	Q1: 1150, Q2: 2950	SO-8FL Dual / DFN-8

For more information please contact your local sales support at www.onsemi.com.

Created on: 7/3/2020